May 1999

National Semiconductor

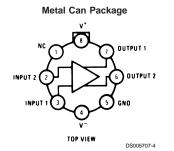
LM160/LM360 High Speed Differential Comparator

General Description

The LM160/LM360 is a very high speed differential input, complementary TTL output voltage comparator with improved characteristics over the μ A760/ μ A760C, for which it is a pin-for-pin replacement. The device has been optimized for greater speed, input different and fan-out, and lower input offset voltage. Typically delay varies only 3 ns for overdrive variations of 5 mV to 400 mV.

Complementary outputs having minimum skew are provided. Applications involve high speed analog to digital convertors and zero-crossing detectors in disk file systems.

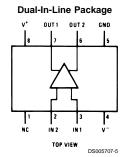
Connection Diagrams



Order Number LM160H/883 (Note 1) or LM360H See NS Package Number H08C

Features

- Guaranteed high speed: 20 ns max
- Tight delay matching on both outputsComplementary TTL outputs
- High input impedance
- Low speed variation with overdrive variation
- Fan-out of 4
- Low input offset voltage
- Series 74 TTL compatible



Order Number LM360M or LM360N See NS Package Number M08A or N08E

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Note 1: Also available in SMD# 5962-8767401

Absolute Maximum Ratings (Notes 6, 8)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Positive Supply Voltage	+8V
Negative Supply Voltage	-8V
Peak Output Current	20 mA
Differential Input Voltage	±5V
Input Voltage	$V^+ \geq V_{\rm IN} \geq V^-$
ESD Tolerance (Note 9)	1600V
Operating Temperature Range	
LM160	-55°C to +125°C
LM360	0°C to +70°C

Storage Temperature Range	–65°C to +150°C			
Lead Temperature				
(Soldering, 10 sec.)	260°C			
Soldering Information				
Dual-In-Line Package				
Soldering (10 seconds)	260°C			
Small Outline Package				
Vapor Phase (60 seconds)	215°C			
Infrared (15 seconds)	220°C			
See AN-450 "Surface Mounting Methods and Their Effect on Product Reliability" for other methods of soldering surface mount devices.				

Electrical Characteristics

 $(\mathsf{T}_{\mathsf{MIN}} \leq \mathsf{T}_{\mathsf{A}} \leq \mathsf{T}_{\mathsf{MAX}})$

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Parameter	Conditio	ons	Min	Тур	Max	Units
Operating Conditions						
Supply Voltage V _{CC} ⁺			4.5	5	6.5	V
Supply Voltage V _{CC} ⁻			-4.5	-5	-6.5	V
Input Offset Voltage	$R_{S} \le 200\Omega$			2	5	mV
Input Offset Current				0.5	3	μA
Input Bias Current				5	20	μA
Output Resistance (Either Output)	V _{OUT} = V _{OH}			100		Ω
Response Time T _A	$T_{A} = 25^{\circ}C, V_{S} = \pm 5V$	(Notes 2, 7)		13	25	ns
	$T_{A} = 25^{\circ}C, V_{S} = \pm 5V$	(Notes 3, 7)		12	20	ns
	$T_{A} = 25^{\circ}C, V_{S} = \pm 5V$	(Notes 4, 7)		14		ns
Response Time Difference between Outputs						
$(t_{pd} \text{ of } +V_{IN1}) - (t_{pd} \text{ of } -V_{IN2})$	T _A = 25°C (Notes 2, 7	7)		2		ns
$(t_{pd} \text{ of } +V_{IN2}) - (t_{pd} \text{ of } -V_{IN1})$	T _A = 25°C (Notes 2, 7	7)		2		ns
$(t_{pd} \text{ of } +V_{IN1}) - (t_{pd} \text{ of } +V_{IN2})$	T _A = 25°C (Notes 2, 7	7)		2		ns
$(t_{pd} \text{ of } -V_{IN1}) - (t_{pd} \text{ of } -V_{IN2})$	T _A = 25°C (Notes 2, 7	7)		2		ns
Input Resistance	f = 1 MHz			17		kΩ
Input Capacitance	f = 1 MHz			3		pF
Average Temperature Coefficient of	$R_{S} = 50\Omega$			8		µV/°C
Input Offset Voltage						
Average Temperature Coefficient of				7		nA/°C
Input Offset Current						
Common Mode Input Voltage Range	$V_{S} = \pm 6.5 V$		±4	±4.5		V
Differential Input Voltage Range			±5			V
Output High Voltage (Either Output)	I_{OUT} = -320 μ A, V _S =	±4.5V	2.4	3		V
Output Low Voltage (Either Output)	$I_{SINK} = 6.4 \text{ mA}$			0.25	0.4	V
Positive Supply Current	$V_{\rm S} = \pm 6.5 V$			18	32	mA
Negative Supply Current	$V_{S} = \pm 6.5 V$			-9	-16	mA
Note 2: Response time measured from the 50% point of Note 3: Response time measured from the 50% point of Note 4: Response time measured from the start of a 100 Note 5: Typical thermal impedances are as follows:	a 2 Vp-p 10 MHz sinusoidal inp	ut to the 50% point of the	output.		c threshold.	
Cavity DIP (J): θ _{jA} 135°C/W	Header (H)	θjA	165°C/W	(Si	till Air)	
Molded DIP (N): θ _{jA} 130°C/W		,	67°C/W	(40	00 LF/min Air F	low)
		θjC	25°C/W			

Note 7: Measurements are made in AC Test Circuit, Fanout = 1

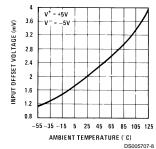
Note 8: Refer to RETS 160X for LM160H, LM160J-14 and LM160J military specifications.

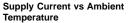
Electrical Characteristics (Continued)

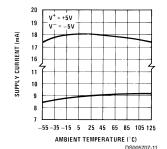
Note 9: Human body model, 1.5 kΩ in series with 100 pF.

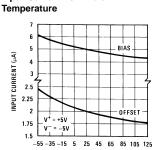
Typical Performance Characteristics

Offset Voltage

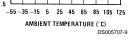




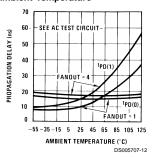


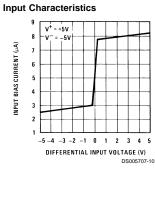


Input Current vs Ambient

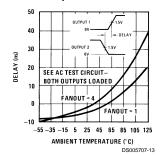




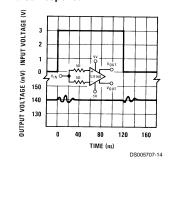


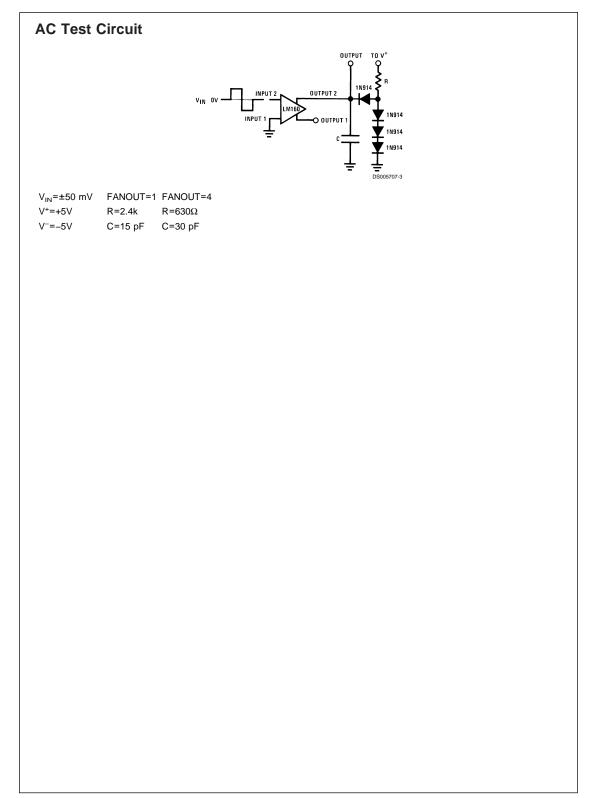


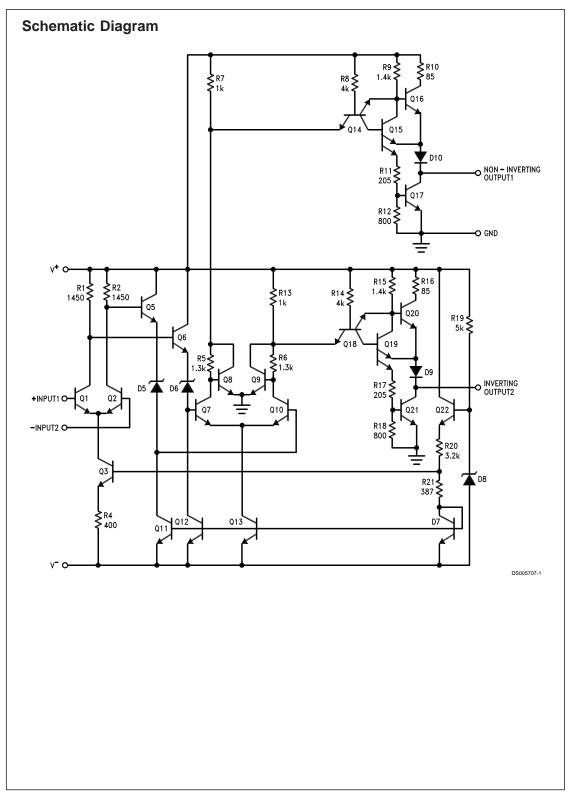
Delay of Output 1 With Respect to Output 2 vs Ambient Temperature

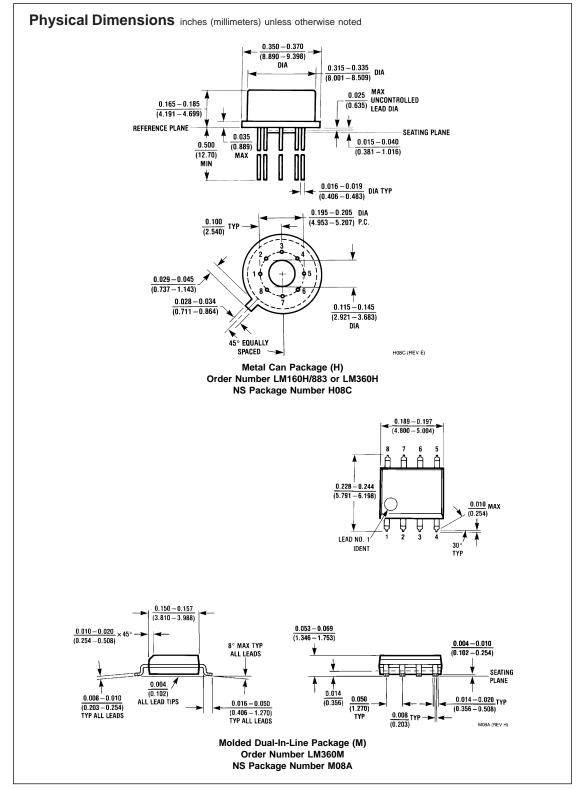


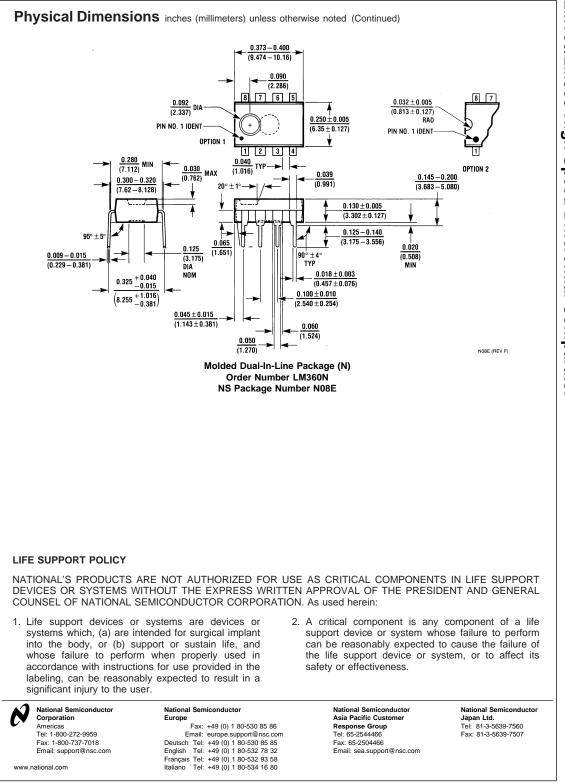
Common-Mode Pulse Response











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